



AP4410BEC

Ultra Low Power Dual Voltage Detector

1. General Description

The AP4410BEC is a voltage detector IC for monitoring battery, power supply and system voltage. The circuit includes dual voltage detection with built-in gate logic and MOSFETs. The AP4410BEC offers ultra-low power consumption that is 0.026 μ A per channel.

The built-in CMOS logic circuit can be controlled independently from the voltage detector. The polarity of the voltage detection results is controlled by pins. This function enables the AP4410BEC as a load switch by using the results of the voltage detection. The AP4410BEC achieves better performance and PCB area than conventional CMOS voltage detector ICs with discrete logics and external MOSFETs.

The AP4410BEC is ideal for voltage conversion or load switch of thin and small wearable devices, over charge/discharge protection of Lithium-ion batteries, power management function of energy harvesting applications.

2. Features

- Power management function
 - Dual voltage detection circuits
 - Control logic with independent power supply
 - Built in P-channel MOSFETs and N-Channel MOSFETs for each channel
- Wide range for detection voltage

Detection voltage "High"	1.8 to 4.4V (Options)
Detection voltage "Low"	1.7 to 4.3V (Options)
- Voltage detection accuracy ± 35 mV
- Ultra-low power consumption 0.026 μ A typical/ch. 0.050 μ A maximum/ch.
- Response Speed 500 μ s maximum
- On resistance

On-chip P-channel MOSFETs	1 Ω typical
On-chip N-channel MOSFETs	2 Ω typical
- Operation temperature -40 - +85 °C
- Package 20-pin WLCSP (1.955 \times 1.555mm, 0.4mm pitch)

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4. Block Diagram

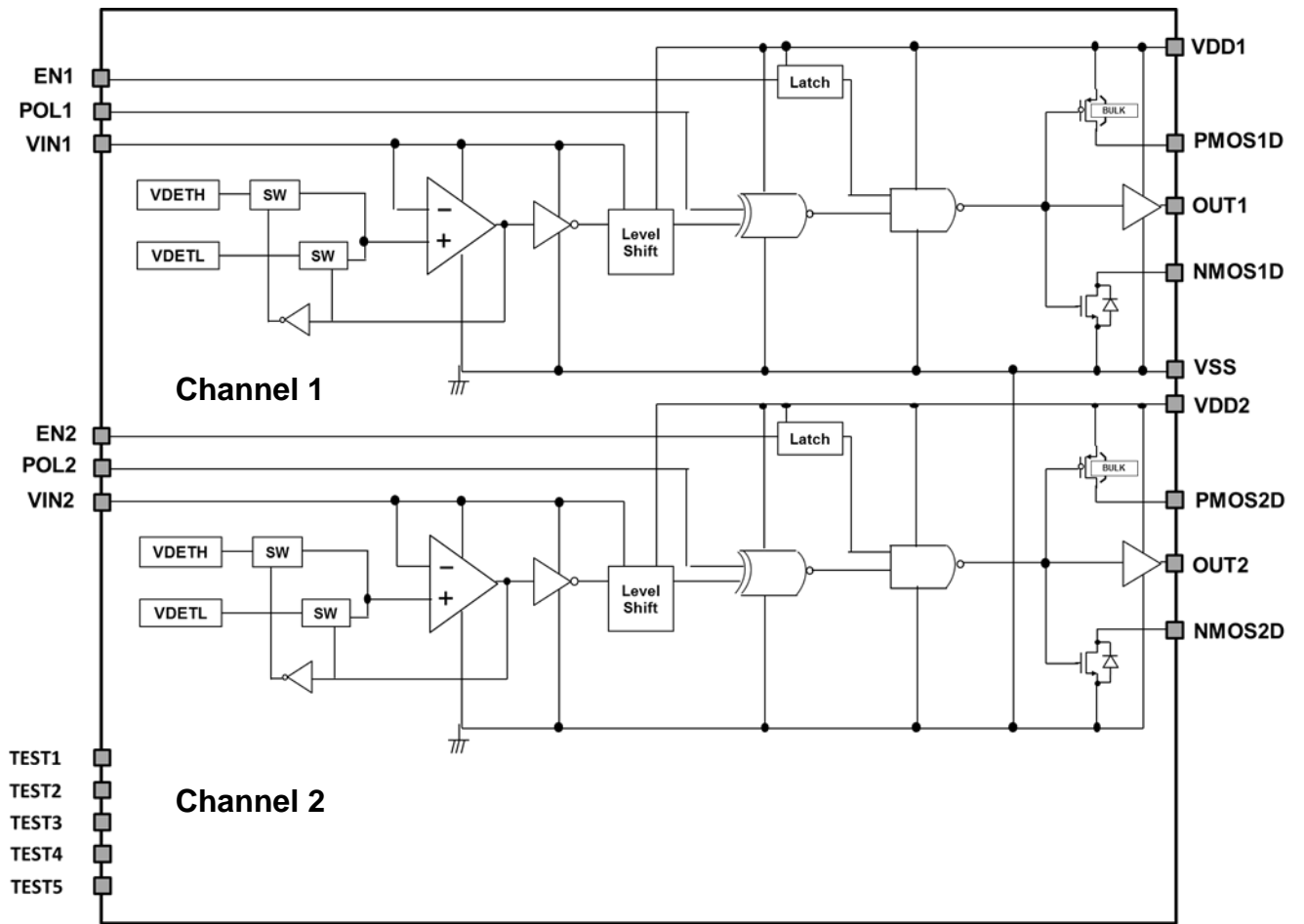
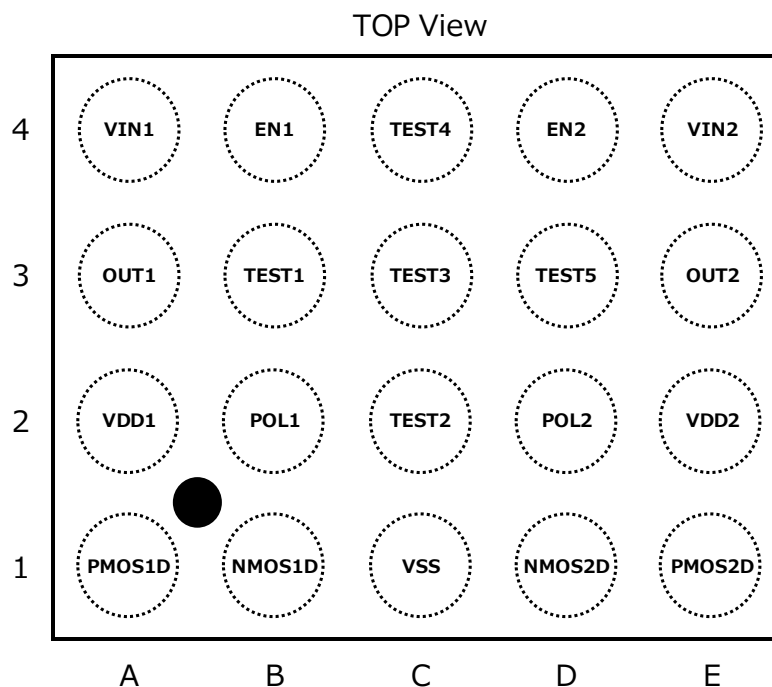


Figure 1. Block Diagram

5. Pin Configuration and Function

■ **Pin Configuration**

• 20-pin WLCSP



■ **Function**

WLCSP Pin	Pin Name	I/O	Function
A1	PMOS1D	Input/Output	PMOS drain pin (Channel 1)
A2	VDD1	Power	Power supply(Channel 1)
A3	OUT1	Output	Logic output (Channel 1)
A4	VIN1	Power	Detection input pin (Channel 1)
B1	NMOS1D	Output	NMOS1 drain pin(Channel 1)
B2	POL1	Input	Polarity cotrol pin (Channel 1)
B3	TEST1	-	For test purposes. This pin should be connected to VSS.
B4	EN1	Input	Enable pin (Channel 1)
C1	VSS	Ground	Ground
C2	TEST2	-	For test purposes. This pin should be connected to VSS.
C3	TEST3	-	For test purposes. This pin should be connected to VSS.
C4	TEST4	-	For test purposes. This pin should be connected to VSS.
D1	NMOS2D	Output	NMOS drain pin(Channel 2)
D2	POL2	Input	Polarity cotrol pin (Channel 2)
D3	TEST5	-	For test purposes. This pin should be connected to VSS.
D4	EN2	Input	Enable pin (Channel 2)
E1	PMOS2D	Input / Output	PMOS drain pin (Channel 2)
E2	VDD2	Power	Power supply(Channel 2)
E3	OUT2	Output	Logic output (Channel 2)
E4	VIN2	Power	Detection input pin (Channel 2)

6. Absolute Maximum Ratings

Parameter	Symbol	min	max	Unit
Pin Voltage (Note 1)	VIN1,VIN2, VDD1,VDD2	-0.3	6.5	V
	OUT1,EN1,POL1	VSS-0.3	VDD1 + 0.3	V
	OUT2,EN2,POL2	VSS-0.3	VDD2 + 0.3	V
	PMOS1D PMOS2D	-0.3	6.5	V
	NMOS1D NMOS2D	-0.3	6.5	V
Power dissipation	Pd	-	0.8	W
Storage Temperature	Tstg	-55	150	°C

Note 1. All voltages are with reference to VSS = 0 V.

WARNING: Stresses exceeding Maximum Ratings may damage the device. Normal operation is not guarantee if the condition exceeds the maximum rating.

7. Recommended Operating Conditions

Parameter	Symbol	min	max	Unit
Operation Temperature	Ta	-40	85	°C
Power Supply Voltage	VIN1 VIN2 VDD1 VDD2	1.2	5.5	V

8. Electrical Characteristics

(Ta= -40 - +85°C, VIN1, VIN2, VDD1 and VDD2 =1.2V to 5.5V, OUT=open, PMOSD=open, NMOSD=open, unless otherwise specified.)

Parameter	Symbol	min	typ	max	Unit	Condition
Detection Voltage "High"	VDETH	V _{DETH} -0.035	V _{DETH}	V _{DETH} +0.035	V	Ta=25°C VIN= "L"→"H" (Note 6)
		V _{DETH} -0.045		V _{DETH} +0.045	V	Ta=85°C VIN= "L"→"H" (Note 6)
Detection Voltage "Low"	VDETL	V _{DETL} -0.035	V _{DETL}	V _{DETL} +0.035	V	Ta=25°C VIN= "H"→"L" (Note 6)
		V _{DETL} -0.045		V _{DETL} +0.045	V	Ta=85°C VIN= "H"→"L" (Note 6)
Power Consumption	IVIN	-	0.026	0.050	μA	Consumption for VIN per channel while the voltage detection circuit is active. (Note 7)
	IVDD (Note 2) (Note 3)	-	0.0001	0.100	μA	Consumption for VDD1 and VDD2. (Note 8)
"High"Level Input Voltage	VIH	VDD ×0.8	-	-	V	
"Low" Level Input Voltage	VIL	-	-	VDD ×0.2	V	
EN pin reverse current (Push, Pull)	I _{EN}	0.15	-	-	μA	
IOH (Note 4)	I _{OH}	0.15	-	-	mA	VIN=V _{DETH} +0.1V, OUT=VDD-0.5V
IOL(Note 4)	I _{OL}	0.2	-	-	mA	VIN=V _{DETL} -0.1V, OUT=0.5V
Response Time (Note 5)	tPLH	-	0.2	0.5	ms	VIN=V _{DETH} -0.1V→V _{DETH} +0.1V
	tPHL	-	0.2	0.5	ms	VIN= V _{DETL} +0.1V→V _{DETL} -0.1V (Note 9)
P-ch MOSFET On-resistance	RonP	-	1	2.3	Ω	VDD ≥ 1.7V
N-ch MOSFET On-resistance	RonN	-	2	5	Ω	VDD ≥ 1.7V

Note 2. Output drive is not included.

Note 3. Total power consumption VDD1 and VDD2 (VDD1+VDD2).

Note 4. Output current depends on VDD1 and VDD2.

IOL shows N-Channel pull current when AP4410BEC OUT1/OUT2 output low.

IOH shows P-Channel push current when AP4410BEC OUT1/OUT2 output high.

Note 5. Response time for OUT1 pin and OUT2 pin

Note 6. Please refer 10. Reference Data (Detection voltage "High" (VDETH) and "Low" (VDETL) vs. Ta)

Note 7. Please refer 10. Reference Data (Current consumption IVIN vs. VIN)

Note 8. Please refer 10. Reference Data (IVDDx vs. Ta)

Note 9. Please refer 10. Reference Data (Response time)

9. Description

■ Voltage Detection Function

VIN1 pin and VIN2 pin = (Abbreviation ;VIN)
 VDD1 pin and VDD2 pin = (Abbreviation ;VDD)
 POL1 pin and POL2 pin = (Abbreviation ;POL)
 EN1 pin and EN2 pin = (Abbreviation ;EN)

- 1) When the input voltage is increasing,
 The OUT1 pin and OUT2 pin(Abbreviation ;OUT) will be in undefined status when VIN voltage is from VSS to AP4410BEC minimum operating voltage(1.2V). The AP4410BEC internal signal A(Please refer Figure 2) outputs VSS when VIN voltage exceeds minimum operating voltage. When VIN voltage reaches to the detection voltage (VDETH), the internal signal A outputs VIN voltage.
- 2) When the input voltage is decreasing,
 When VIN voltage is higher than VDETH, internal signal A outputs VIN. When VIN goes under the detection voltage (VDETL), OUT outputs VSS. The internal signal A will be undefined status when VIN voltage becomes lower than AP4410BEC minimum operating voltage(1.2V).

The logic inputs POL and EN become valid when VDD voltage exceeds 1.2V which is the AP4410BEC minimum operation voltage. In case of POL = "L", EN="H", OUT behaves as Figure. 3. The AP4410BEC is able to output the inverted results of the voltage detection using POL. EN can control P-channel MOSFET and N-channel MOSFET ON and OFF. EN has latch function so that it keeps its present state if the input becomes Hi-Z. The BULK of the P-channel MOSFET is connected to the higher voltage pin between VDD and PMOSD.

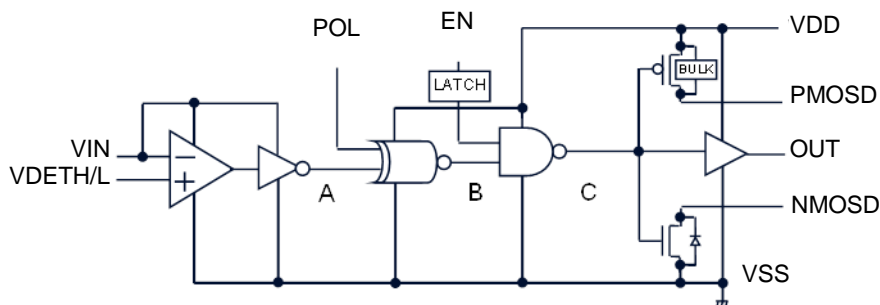


Figure 2. Block Diagram of Control Logic Part (Each channel)

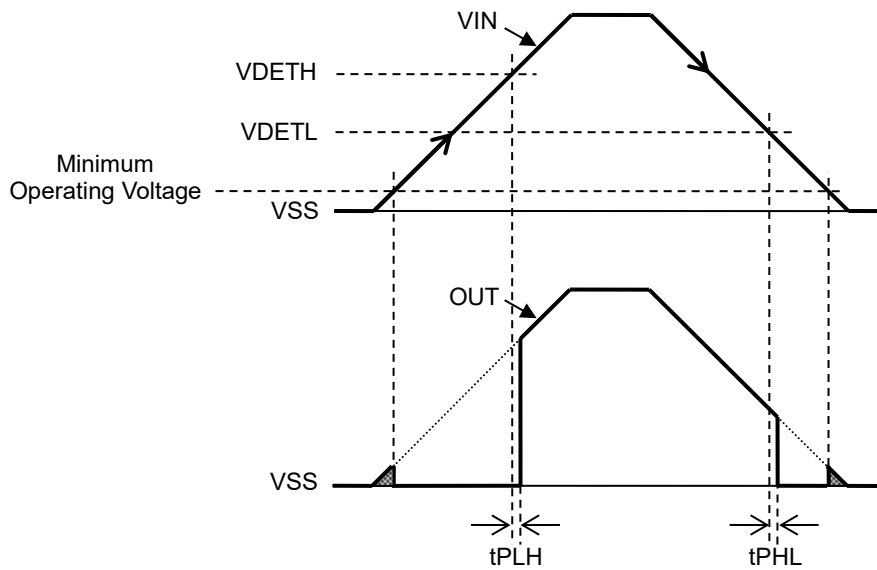


Figure 3. Function of AP4410BEC voltage detection

Table 1. Control logic truth table (Note 10)

POL input	VIN	EN input	Internal signal A	Internal signal B	Internal signal C	PMOSD	NMOSD	OUT	Note
L	$V_{IN} < V_{DETH}$	L	L	H	H	OPEN	L	H	-
L	$V_{IN} < V_{DETH}$	H	L	H	L	H	OPEN	L	OUT= positive polarity
L	$V_{IN} \geq V_{DETH}$	H	H	L	H	OPEN	L	H	
L	$V_{IN} \geq V_{DETH}$	L	H	L	H	OPEN	L	H	-
H	$V_{IN} < V_{DETH}$	L	L	L	H	OPEN	L	H	-
H	$V_{IN} < V_{DETH}$	H	L	L	H	OPEN	L	H	OUT= negative polarity
H	$V_{IN} \geq V_{DETH}$	H	H	H	L	H	OPEN	L	
H	$V_{IN} \geq V_{DETH}$	L	H	H	H	OPEN	L	H	-

Note 10. When the VIN voltage is increasing from VDETL or lower.

Table 2 Control logic truth table (Note 11)

POL input	VIN	EN input	Internal signal A	Internal signal B	Internal signal C	PMOSD	NMOSD	OUT	Note
L	$V_{IN} > V_{DETL}$	L	H	L	H	OPEN	L	H	-
L	$V_{IN} > V_{DETL}$	H	H	L	H	OPEN	L	H	OUT= positive polarity
L	$V_{IN} \leq V_{DETL}$	H	L	H	L	H	OPEN	L	
L	$V_{IN} \leq V_{DETL}$	L	L	H	H	OPEN	L	H	-
H	$V_{IN} > V_{DETL}$	L	H	H	H	OPEN	L	H	-
H	$V_{IN} > V_{DETL}$	H	H	H	L	H	OPEN	L	OUT= negative polarity
H	$V_{IN} \leq V_{DETL}$	H	L	L	H	OPEN	L	H	
H	$V_{IN} \leq V_{DETL}$	L	L	L	H	OPEN	L	H	-

Note 11. When the VIN voltage is decreasing from VDETH or higher.

10. Reference Data

■ Detection Voltage “High” (VDETH) and “Low” (VDETL) vs. VIN

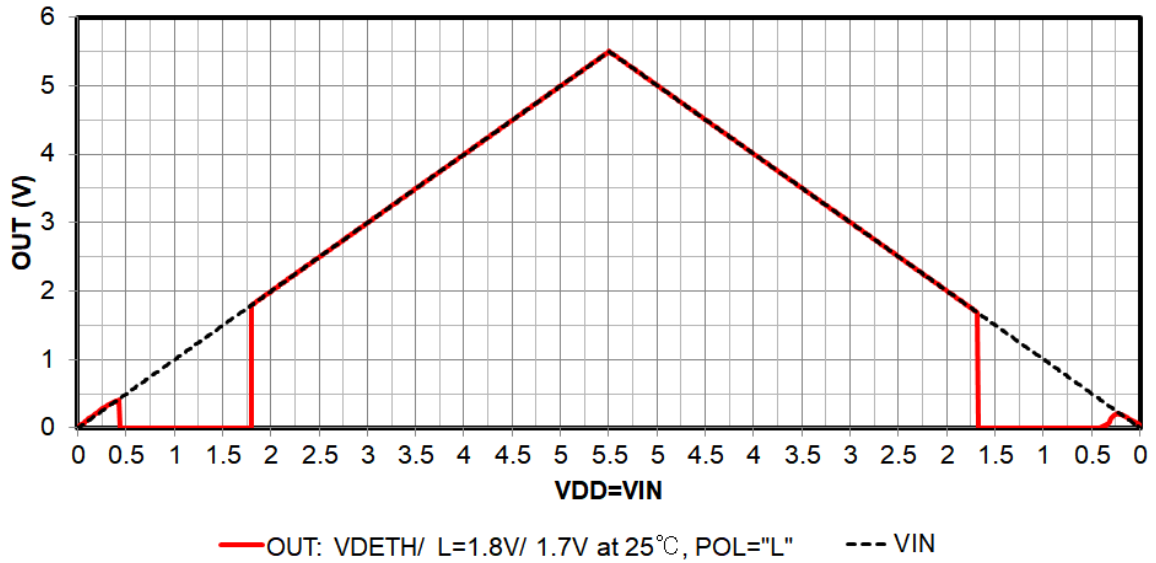


Figure 4. VDETH=1.8V, VDETL=1.7V (POL="L")

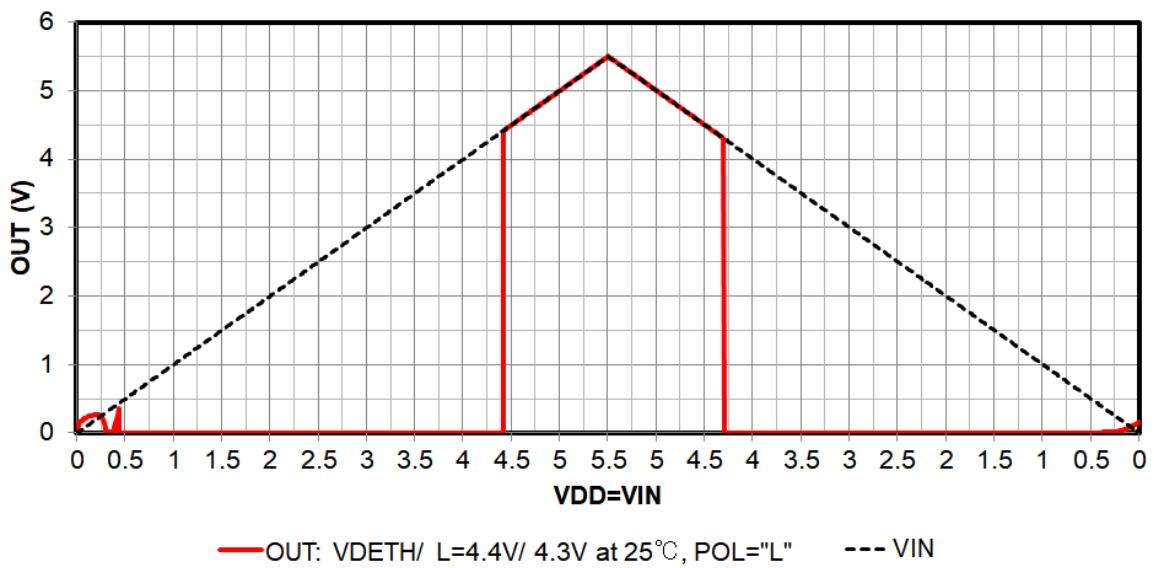


Figure 5. VDETH=4.4V, VDETL=4.3V (POL="L")

■ Detection voltage “High” (VDETH) and “Low” (VDETL) vs. Ta

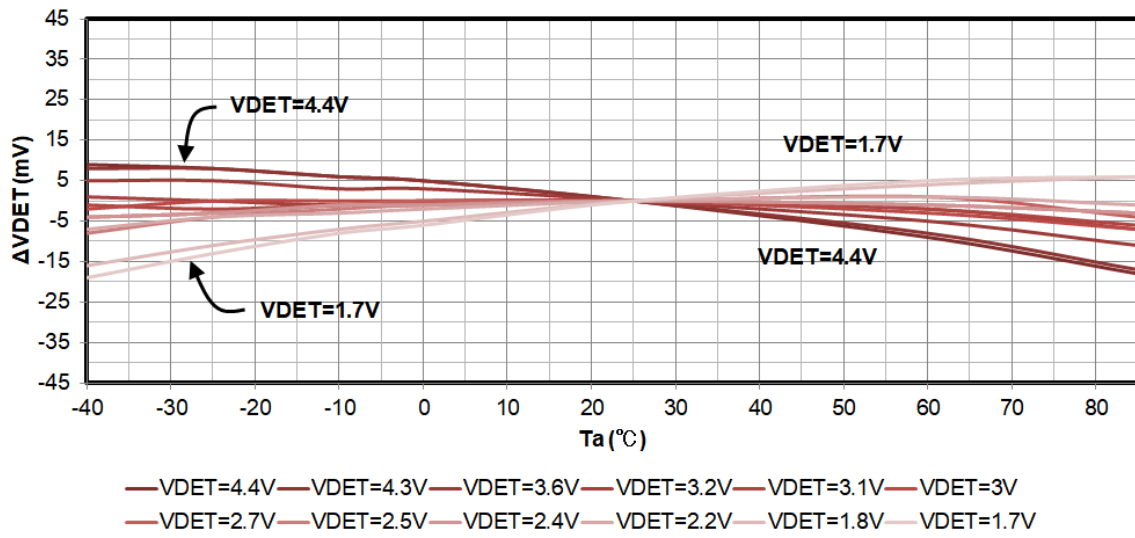


Figure 6. ΔV_{DET} (mV) vs. T_a normalized to 25°C

■ Current consumption IVIN vs. VIN

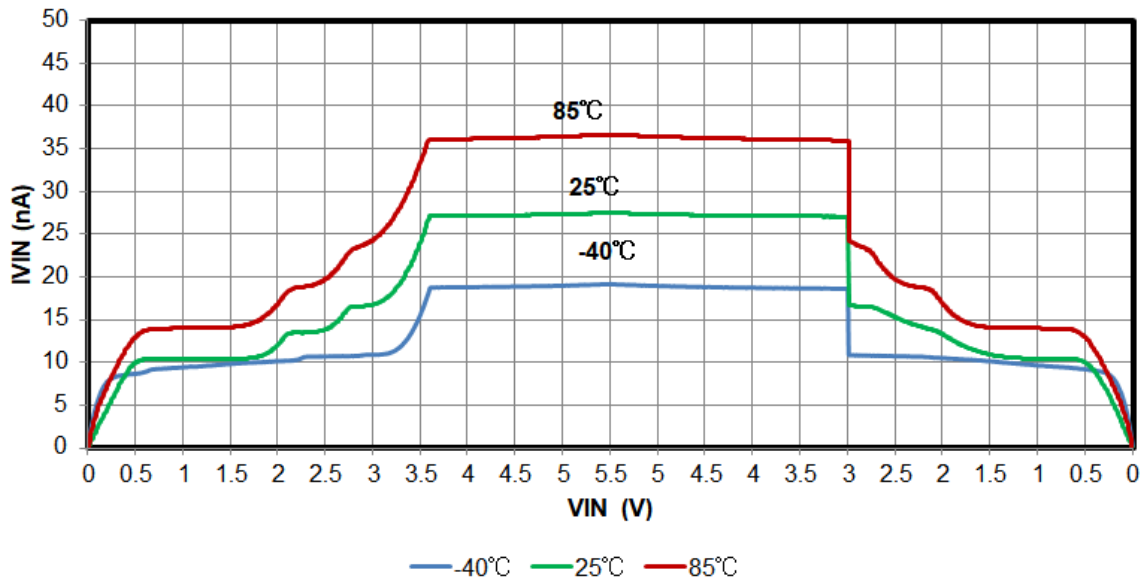


Figure 7. VDETH=3.6V, VDETL=3.0V (POL="L")

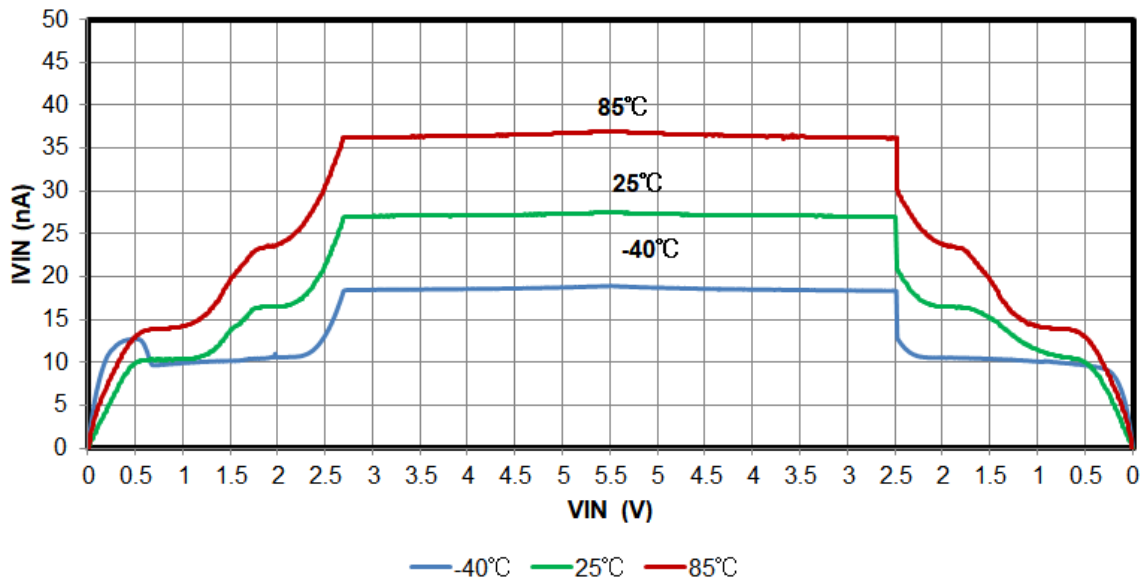


Figure 8. VDETH=2.7V, VDETL=2.5V (POL="L")

■ Current consumption vs. Ta

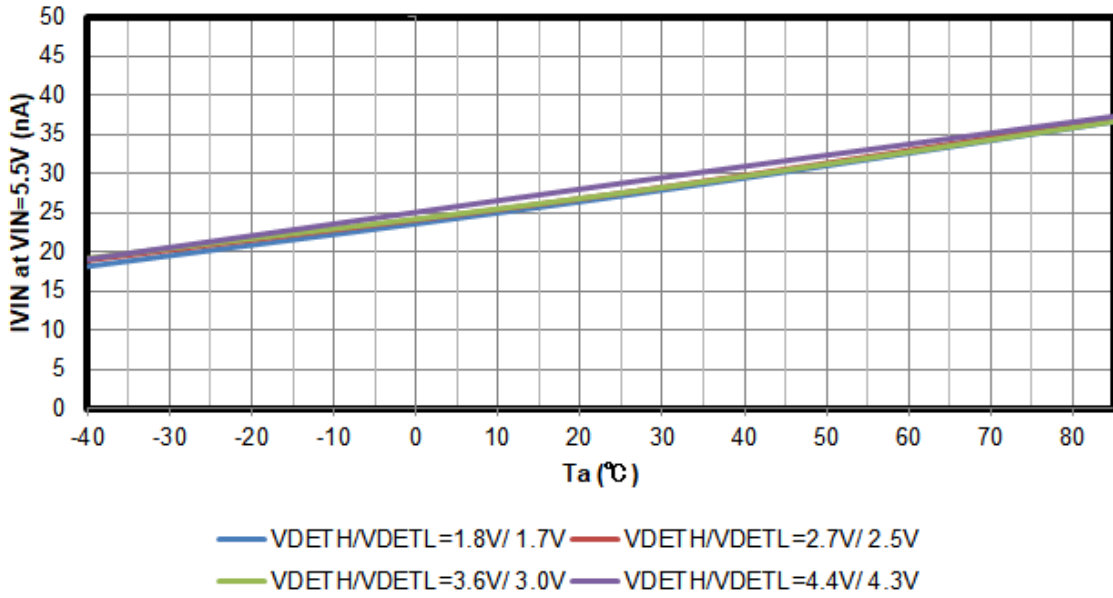


Figure 9. IVIN vs. Ta (VIN=5.5V, POL="L")

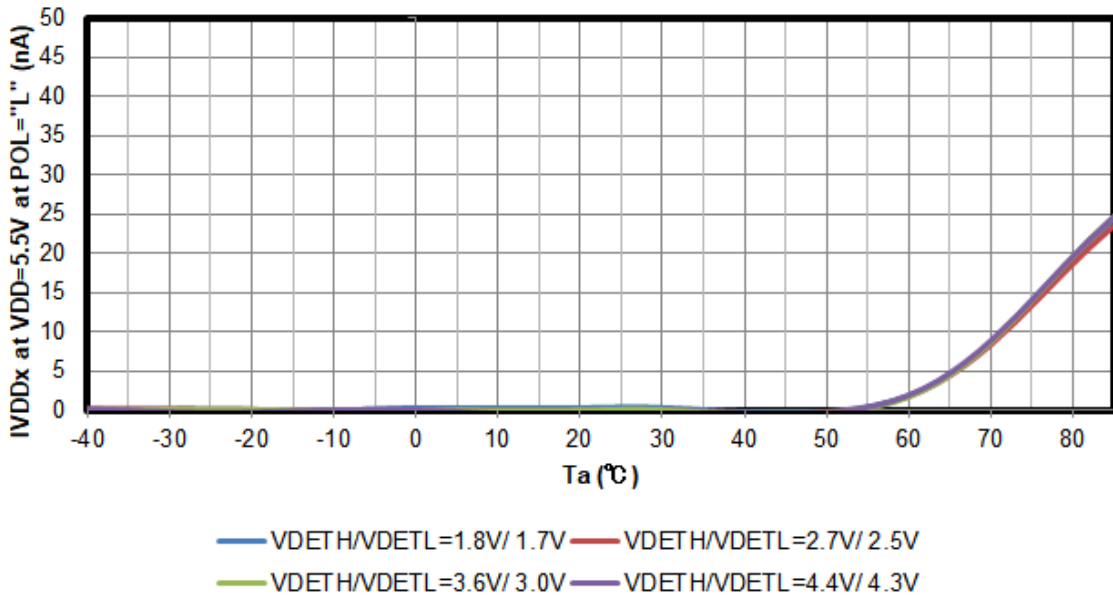


Figure 10. IVDDx vs. Ta (VDD=5.5V, POL="L")

Note 12. IVDDx is current consumption of each channel VDD1 and VDD2

■ Response time (tPLH, tPHL)

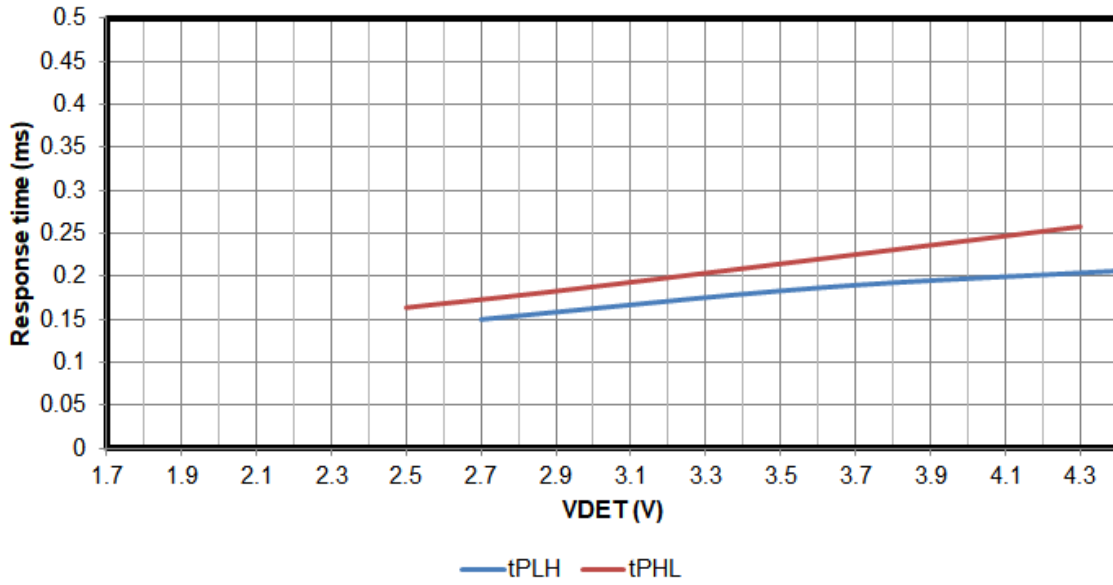


Figure 11. VDET vs. tPLH & tPHL (25°C, POL="L")

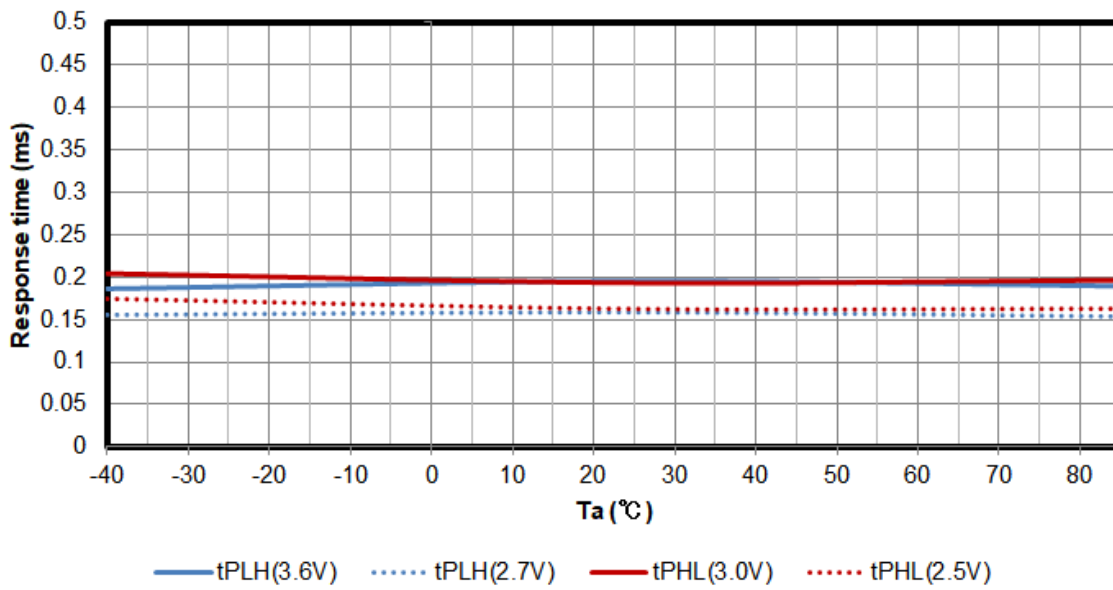


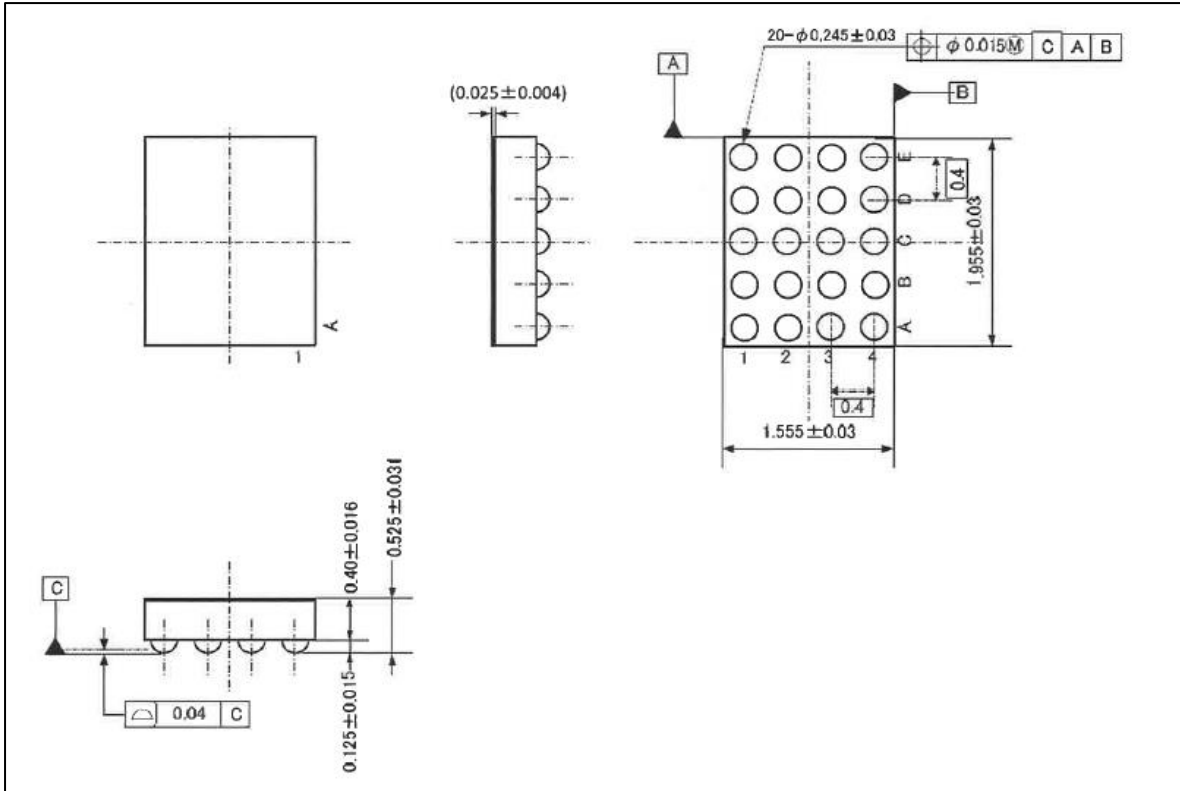
Figure 12. VDET vs. Ta (POL="L")

11. Package

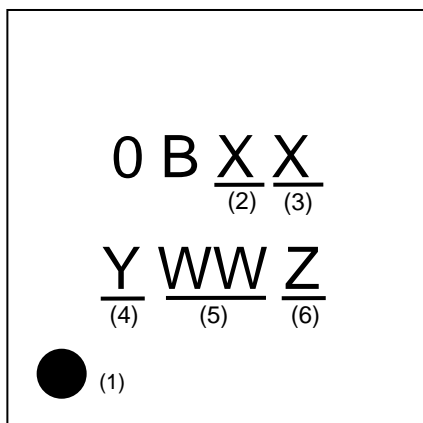
■ **Outline Dimensions**

20-pin WLCSP (Unit: mm)

When the IC is exposed to light, it might affect the electrical characteristics of the IC due to the light sensitivity of WLCSP package structures.



■ **Marking**



- (1) 1 Pin Indication
- (2) Symbol of the detection voltage of system 1
- (3) Symbol of the detection voltage of system 2
- (4) Year code (last 1 digit)
- (5) Week code
- (6) Management code

12. Revision History

Date (YY/MM/DD)	Revision	Page	Contents
2018/05/17	00	-	First Edition

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